

ABSTRACT OF THE DISCLOSURE

A self-pulsating semiconductor laser device includes a semiconductor substrate of the first conductivity type, a first cladding layer of the first conductivity type formed on the substrate and an active layer formed on the first cladding layer. A second cladding layer of a second conductivity type is formed on the active layer. A saturable absorbing layer is formed on at least portions of at least one of the first cladding layer and the second cladding layer. The saturable absorbing layer has a band gap energy either approximately the same as, or slightly smaller than, the active layer.